

IN THE SPECIFICATION

Please amend paragraph [0012] in the published specification, as follows:

[0012]

(ii) Particularly in thin layers, the ~~electric field~~ biased voltage applied to the diamond may be less than 300 V, and preferably less than 200 V, and more preferably less than 100 V, and most preferably less than 75 V. The diamond layer operated under [[the]] these applied voltages preferably operates at better than 80%, and more preferably better than 90%, and most preferably at better than 95% of the saturated charge collection efficiency.